MOSFETs Silicon N-Channel MOS

# T2N7002BK

### 1. Applications

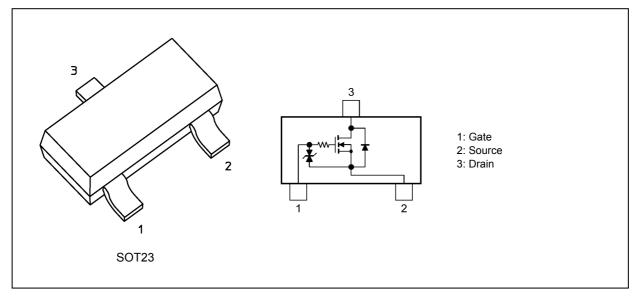
High-Speed Switching

### 2. Features

- (1) Low drain-source on-resistance
  - :  $\mathrm{R}_{\mathrm{DS(ON)}} = 1.05~\Omega$  (typ.) (@V\_{\mathrm{GS}} = 10~V)
  - $\mathrm{R}_{\mathrm{DS(ON)}}=1.15~\Omega$  (typ.) (@V\_{\mathrm{GS}}=5.0~V)

 $\mathrm{R}_{\mathrm{DS(ON)}}$  = 1.2  $\Omega$  (typ.) (@V\_{\mathrm{GS}} = 4.5 V)

### 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	60	V
Gate-source voltage		V <sub>GSS</sub>	±20	
Drain current (DC)	(Note 1)	I <sub>D</sub>	400	mA
Drain current (pulsed)	(Note 1), (Note 2)	I <sub>DP</sub>	1200	
Power dissipation	(Note 3)	PD	320	mW
Power dissipation	(Note 4)		1000	]
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Repetitive rating; pulse width limited by maximum channel temperature.

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pulse width \leq 10 \mu s, Duty \leq 1 %
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- Note 3: Device mounted on a 25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm FR-4 glass epoxy board (Cu pad: 0.42 mm<sup>2</sup>  $\times$  3)
- Note 4: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR-4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

### 5. Electrical Characteristics

## 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25$ °C)

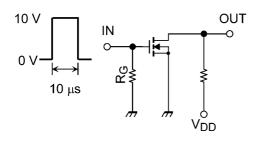
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}$ = ±16 V, $V_{DS}$ = 0 V	_	_	±10	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V	60	—	—	V
Gate threshold voltage		V <sub>th</sub>	$I_D$ = 250 $\mu$ A, $V_{DS}$ = $V_{GS}$	1.1	_	2.1	]
Drain-source on-resistance	(Note 1)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 10 V		1.05	1.5	Ω
			I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 5.0 V	_	1.15	1.65	
			I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 4.5 V		1.2	1.75	
Forward transfer admittance	(Note 1)	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 200 mA	_	1.0	_	S

Note 1: Pulse measurement.

## 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,	—	26	40	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	1.3	_	
Output capacitance	C <sub>oss</sub>	]	—	5.5	_	]
Switching time (rise time)	tr	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 200 mA	_	3.6	_	ns
Switching time (turn-on delay time)	t <sub>d(on)</sub>	$V_{GS}$ = 0 to 10 V, R <sub>G</sub> = 50 Ω Duty ≤ 1 %, V <sub>IN</sub> : t <sub>r</sub> , t <sub>f</sub> < 5 ns,	_	5.5	11	
Switching time (fall time)	t <sub>f</sub>	Common source, See Chapter 5.3.	—	17	_	]
Switching time (turn-off delay time)	t <sub>d(off)</sub>	]		38	90	

## 5.3. Switching Time Test Circuit



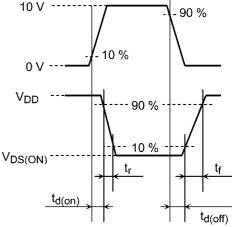


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25$ °C)

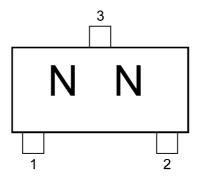
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DS}$ = 30 V, $V_{GS}$ = 4.5 V,	_	0.39	0.6	nC
Gate-source charge	Q <sub>gs</sub>	I <sub>D</sub> = 200 mA	_	0.2	—	
Gate-drain charge	Q <sub>gd</sub>		_	0.11		

## 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

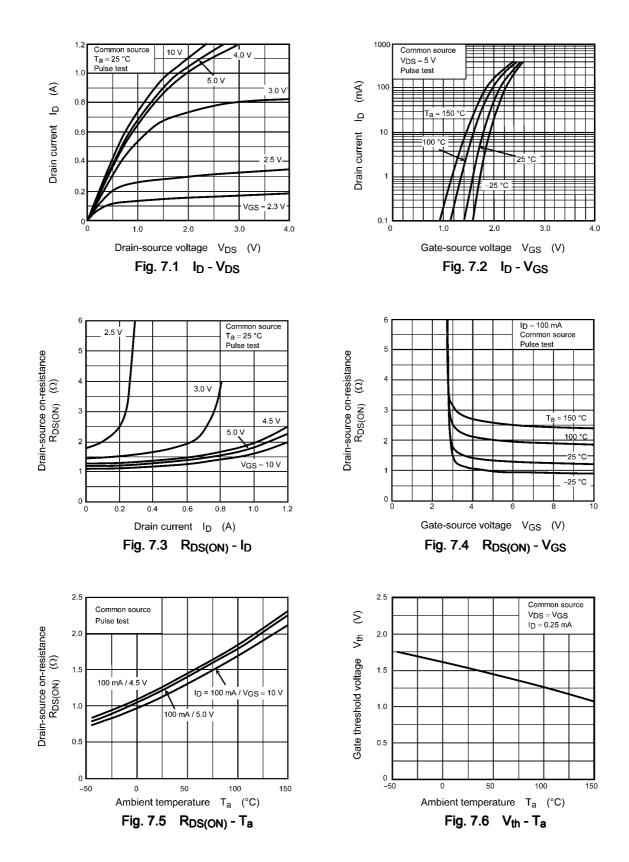
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{\text{DSF}}$	I <sub>D</sub> = -115 mA, V <sub>GS</sub> = 0 V		-0.79	-1.1	V

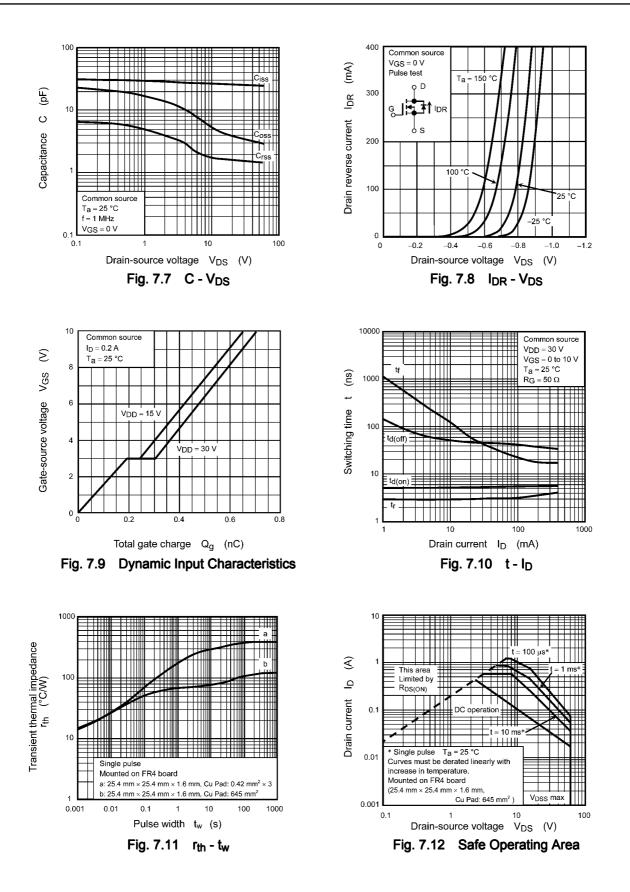
Note 1: Pulse measurement.

#### 6. Marking



## 7. Characteristics Curves (Note)





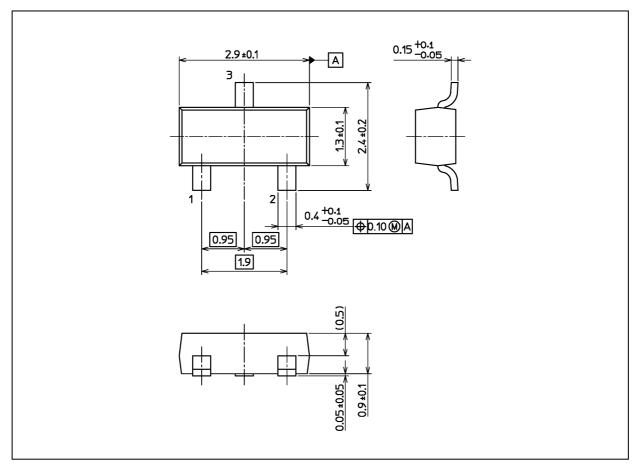
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## T2N7002BK

#### **Package Dimensions**

Unit: mm



Weight: 9 mg (typ.)

	Package Name(s)
Nickname: SOT23	

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